

Press Fit Diode, 50A

Features

- Low Leakage
- Low Forward Voltage Drop
- Low Cost
- High Surge Current Capability

Mechanical Characteristics

- **Chip:** Gpp Chip
- **Encapsulation:** Epoxy Sealed
- **Lead:** Plated Lead, Solderable
- **Mounting:** Press Fit
- **Weight:** 6.5 grams (approx.)

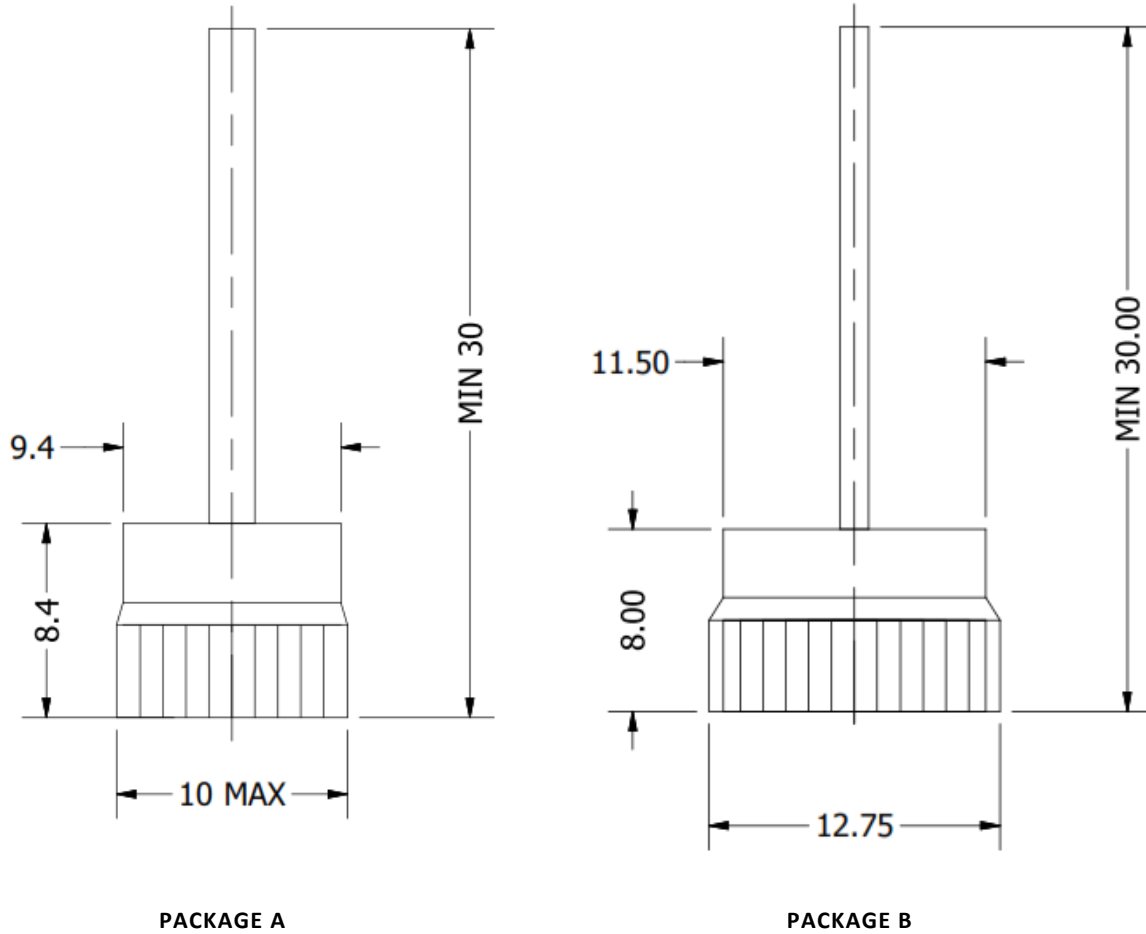


PRESS-FIT DIODE

Electrical Characteristics ($T_A = 25^{\circ}\text{C}$ unless otherwise specified)					
Parameter	Symbol	NP5002(R)	NP5004(R)	NP5006(R)	Units
Maximum repetitive peak reverse voltage	V_{RRM}	200	400	600	V
Maximum RMS Voltage	V_{RMS}	140	280	420	V
Maximum DC Blocking Voltage	V_{DC}	200	400	600	V
Maximum average forward output current @ $T_A = 105^{\circ}\text{C}$	$I_{F(AV)}$	50			A
Peak forward surge current (8.3ms) single half sine-wave superimposed on rated load	I_{FSM}	600			A
Maximum instantaneous forward voltage drop @ 100 A	V_F	1.1			V
Maximum DC reverse current at rated DC blocking voltage	I_R	$T_A = 25^{\circ}\text{C}$	5.0		μA
		$T_A = 100^{\circ}\text{C}$	450		
Typical Thermal Resistance	$R_{\theta(j-c)}$	0.8			$^{\circ}\text{C}/\text{W}$
Operating and storage temperature	T_J, T_{STG}	-65 to +175			$^{\circ}\text{C}$

Package Outline

(All dimensions in mm)



Ordering Table

NP	50	02	R
1	2	3	4

1 – Press-fit Diode

2 – Current Rating = $I_{F(AV)}$

3 – Voltage, V_{RRM} (as per table)

4 – Polarity:

- > None = Normal (Cathode to Base) (**Red** Color Epoxy)
- > R = Reverse (Anode to Base) (**Black** Color Epoxy)